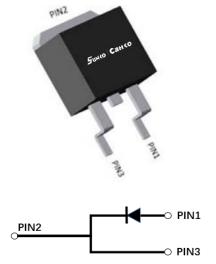


Silicon Carbide Schottky Diode

V _{RRM}	650 V
I _F (135°C)	10 A
Qc	25 nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-263 Molding compound meets UL 94 V-0 flammability rating, -, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106506BQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C			21
Continuous forward current @ T _c =135°C	IF	А	10
Continuous forward current @ T _c =157°C			6
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	65
Power Dissipation@ T _c =25°C	D	w	84
Power Dissipation@ T _c =110°C	P _{TOT}		36
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	21
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



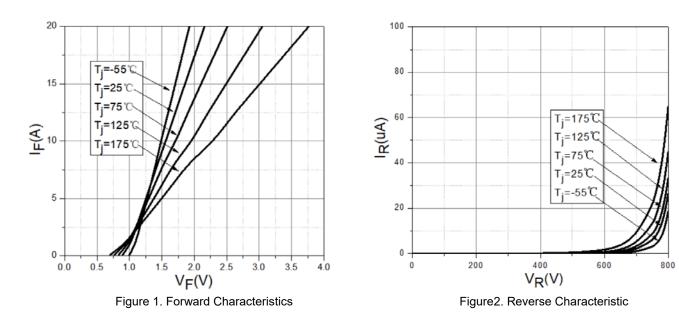
Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	v	I _F =6A, T _j =25°C	1.31	1.5
			I _F =6A, T _j =175°C	1.65	-
Reverse leakage current	1	μΑ	V _R =650V, T _j =25°C	0.5	25
	I _R		V _R =650V, T _j =175°C	5	-
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= \int_0^{VR} C(V)dV	25	-
Total capacitance C		pF	V _R =0V, f=1MHZ	378	-
	С		V _R =200V, f=1MHZ	51	-
			V _R =400V, f=1MHZ	49	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{8J-C}	°C <i>W</i>	1.75

■Typical Characteristics



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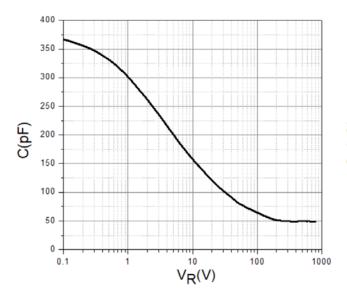
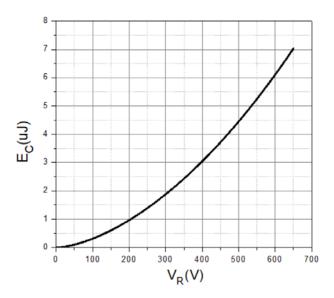
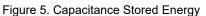
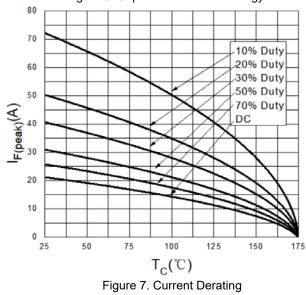


Figure 3. Capacitance vs. Reverse Voltage







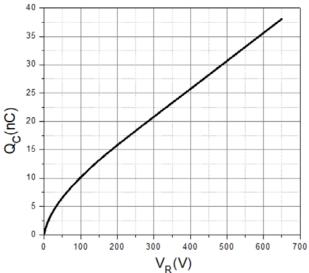
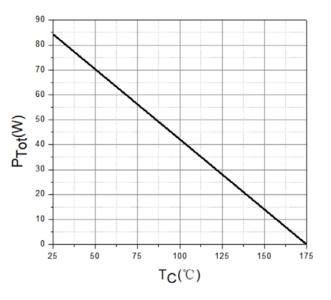
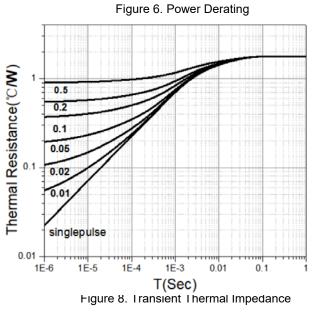


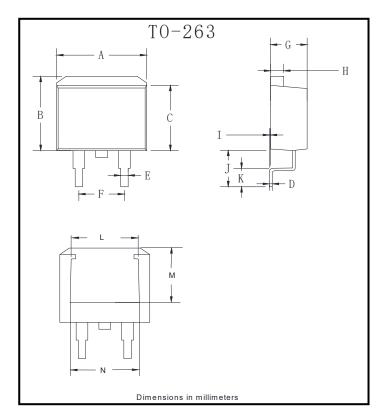
Figure 4. Total Capacitance Charge vs. Reverse Voltage







Outline Dimensions



TO-263				
Dim	Min	Max		
А	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
E	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
К	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
Ν	7.6	8.2		

Shanghai Sunco Electronics Co., Ltd



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